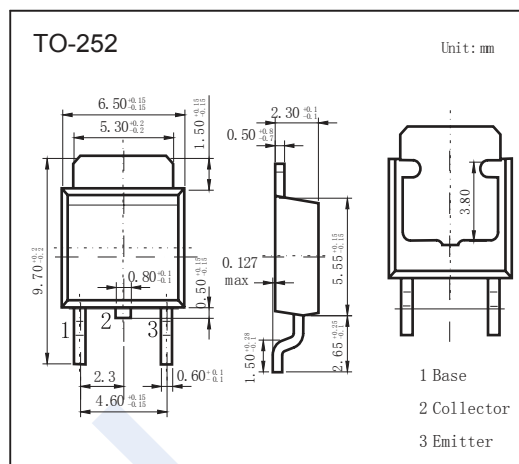


PNP Transistors

2SB1266

■ Features

- Suitable for sets whose height is restricted
- Complementary to 2SD1902

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-60	V
Collector - Emitter Voltage	V_{CE0}	-60	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-3	A
Collector Current - Pulse	I_{CP}	-8	
Collector Power Dissipation $T_c = 25^\circ\text{C}$ $T_a = 25^\circ\text{C}$	P_C	30	W
		1.65	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -1\text{ mA}, I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -5\text{ mA}, R_{BE} = \infty$	-60			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -1\text{ mA}, I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-100	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{ A}, I_B = -200\text{ mA}$		-0.4	-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{ A}, I_B = -200\text{ mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$			-1	
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$	70		280	
		$V_{CE} = -5\text{ V}, I_C = -3\text{ A}$	20			
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		60		pF
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$		8		MHz

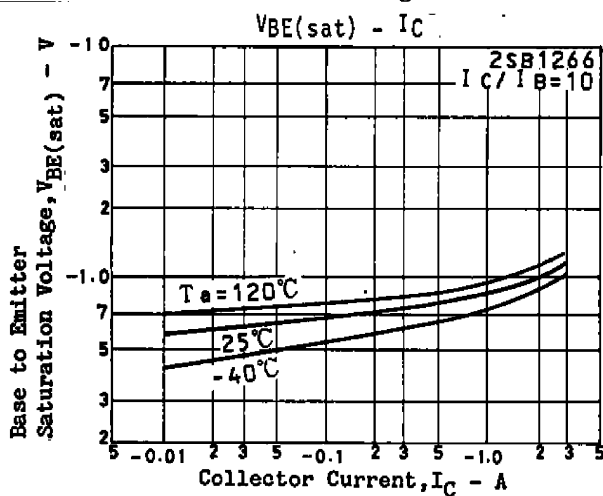
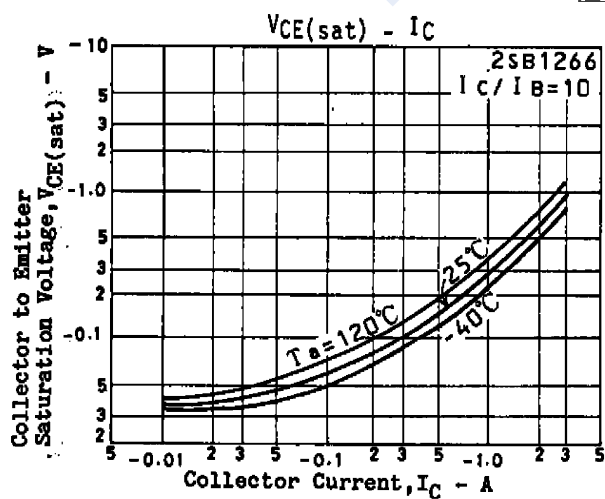
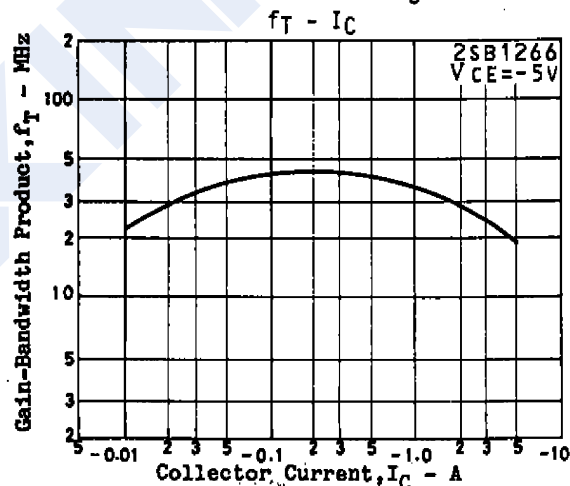
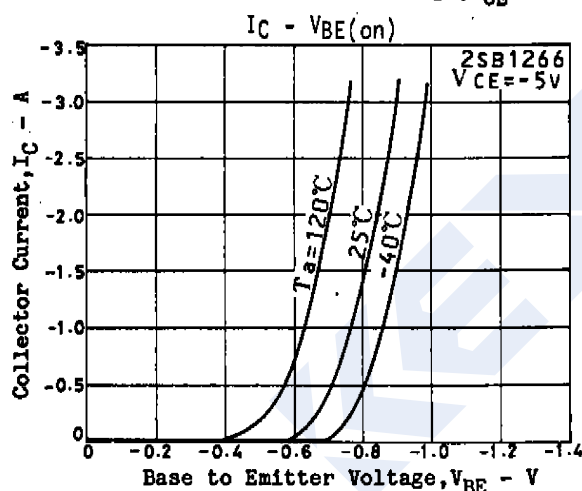
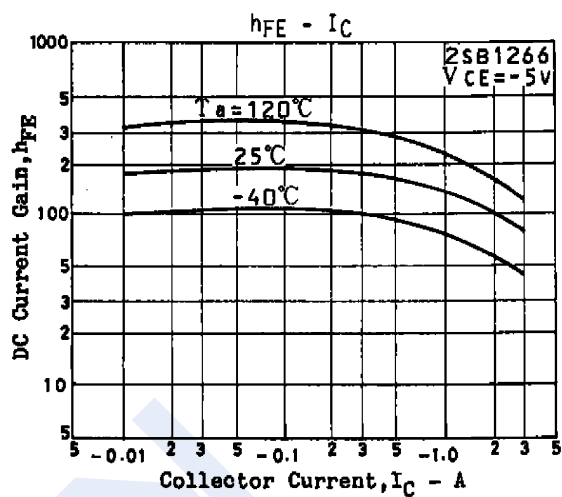
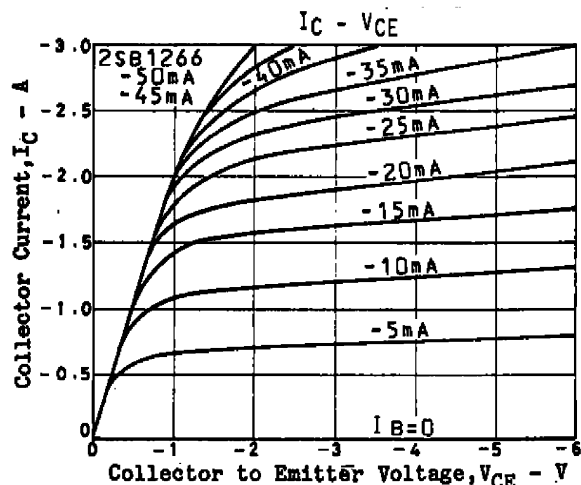
■ Classification of $h_{FE(1)}$

Type	2SB1266-Q	2SB1266-R	2SB1266-S
Range	70-140	100-200	140-280

PNP Transistors

2SB1266

■ Typical Characteristics



PNP Transistors

2SB1266

■ Typical Characteristics

